

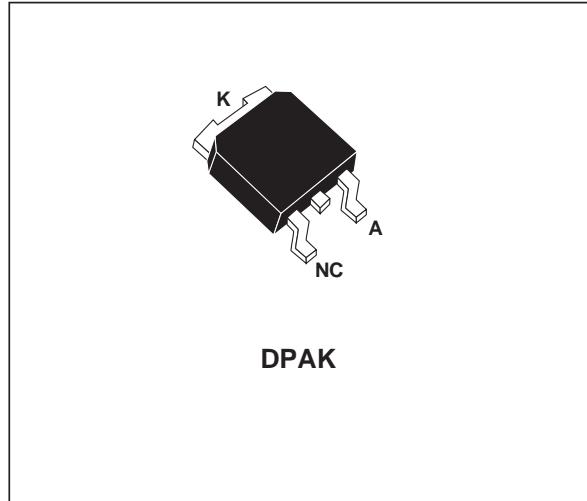
HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	5 A
V_{RRM}	100 V
$T_j(\text{max})$	175 °C
$V_F(\text{max})$	0.61 V

FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- HIGH JUNCTION TEMPERATURE CAPABILITY
- LOW LEAKAGE CURRENT
- GOOD TRADE OFF BETWEEN LEAKAGE CURRENT AND FORWARD VOLTAGE DROP
- AVALANCHE CAPABILITY SPECIFIED



DESCRIPTION

Schottky barrier rectifier designed for high frequency miniature Switched Mode Power Supplies such as adaptors and on board DC to DC converters.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	100	V
$I_{F(RMS)}$	RMS forward current	10	A
$I_{F(AV)}$	Average forward current	5	A
I_{FSM}	Surge non repetitive forward current	75	A
I_{RRM}	Repetitive peak reverse current	1	A
I_{RSM}	Non repetitive peak reverse current	2	A
P_{ARM}	Repetitive peak avalanche power	7200	W
T_{stg}	Storage temperature range	- 65 to + 175	°C
T_j	Maximum operating junction temperature *	175	°C
dV/dt	Critical rate of rise of reverse voltage	10000	V/μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j - a)}$ thermal runaway condition for a diode on its own heatsink

STPS5H100B

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	2.5	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R *	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			3.5	µA
		$T_j = 125^\circ\text{C}$			1.3	4.5	mA
V_F **	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 5 \text{ A}$			0.73	V
		$T_j = 125^\circ\text{C}$	$I_F = 5 \text{ A}$		0.57	0.61	
		$T_j = 25^\circ\text{C}$	$I_F = 10 \text{ A}$			0.85	
		$T_j = 125^\circ\text{C}$	$I_F = 10 \text{ A}$		0.66	0.71	

Pulse test : * $t_p = 5 \text{ ms}, \delta < 2\%$

** $t_p = 380 \mu\text{s}, \delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = 0.51 \times I_{F(AV)} + 0.02 \times I_F^2 (\text{RMS})$$

Fig. 1: Average forward power dissipation versus average forward current.

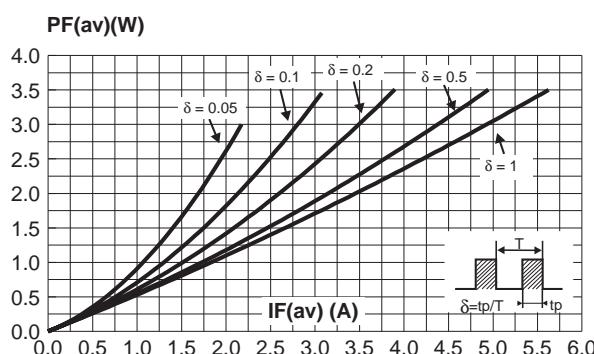


Fig. 3: Normalized avalanche power derating versus pulse duration.

Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$).

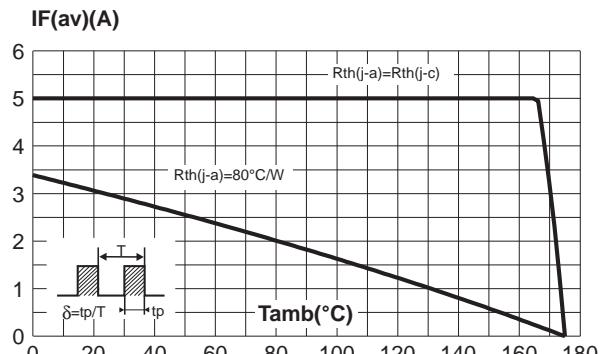


Fig. 4: Normalized avalanche power derating versus junction temperature.

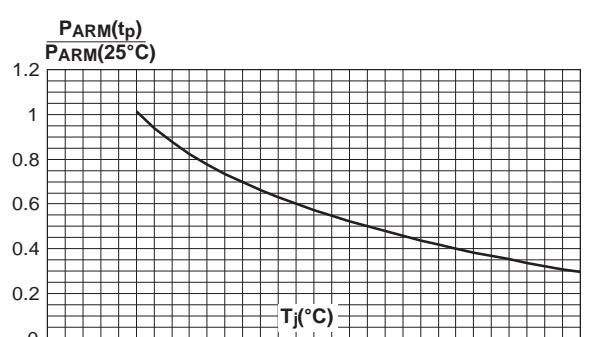
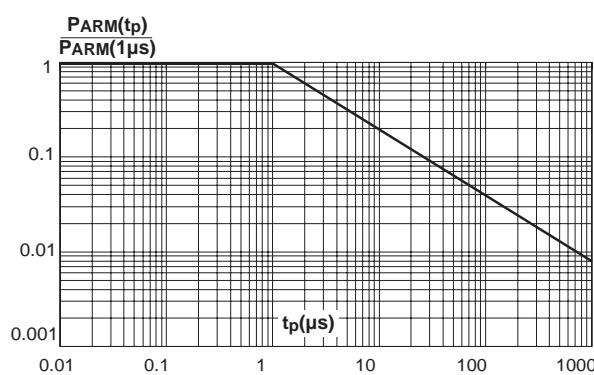


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values).

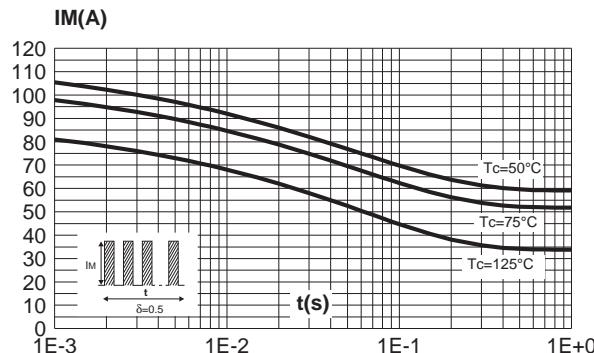


Fig. 7: Reverse leakage current versus reverse voltage applied.

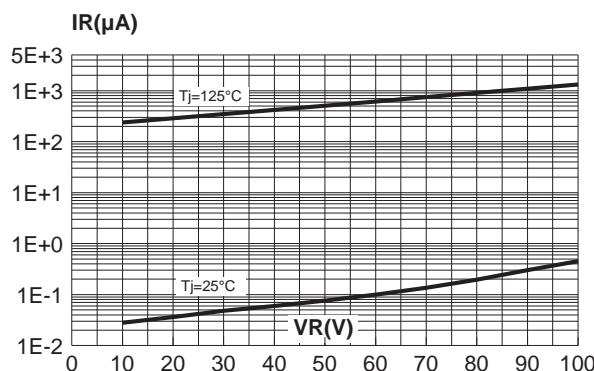


Fig. 9: Forward voltage drop versus forward current (maximum values).

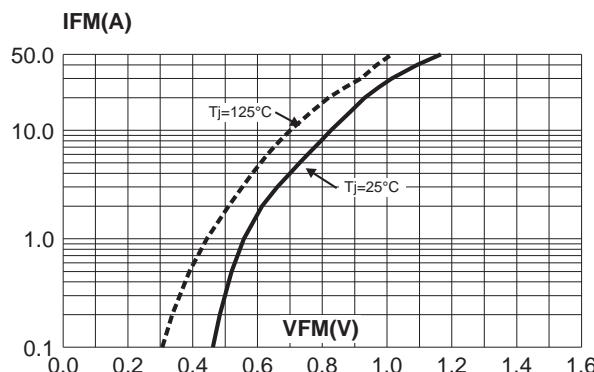


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

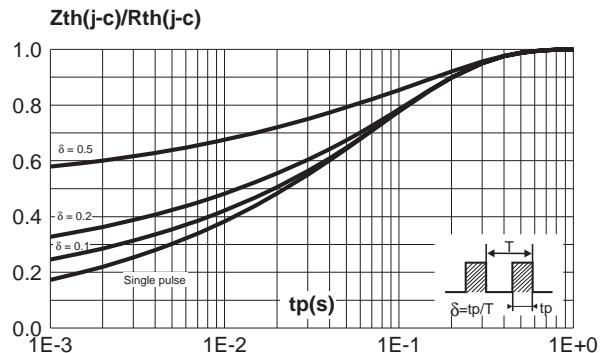


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).

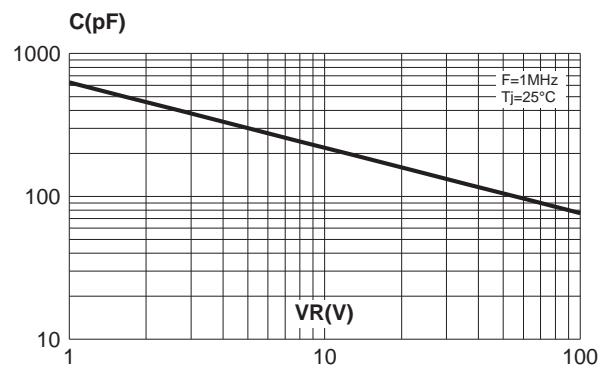
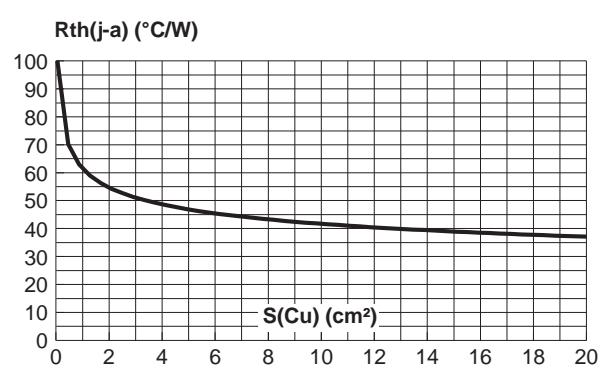


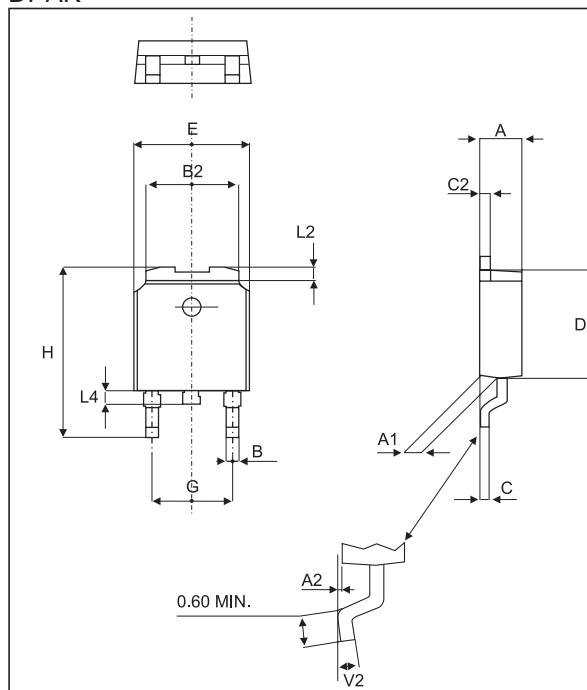
Fig. 10: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: $35\mu\text{m}$).



STPS5H100B

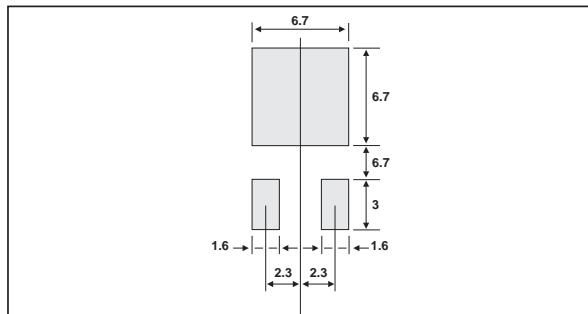
PACKAGE MECHANICAL DATA

DPAK



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.212
C	0.45		0.60	0.017		0.023
C2	0.48		0.60	0.018		0.023
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.251		0.259
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.397
L2		0.80			0.031	
L4	0.60		1.00	0.023		0.039
V2	0°		8°	0°		8°

FOOT PRINT (in millimeters)



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS5H100B	S5H100	DPAK	0.30g	75	Tube
STPS5H100B-TR	S5H100	DPAK	0.30g	2500	Tape & reel

■ EPOXY MEETS UL94,V0

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